

# ISL9K860P3

# 8A, 600V Stealth™ Dual Diode

# General Description

The ISL9K860P3 is a Stealth™ dual diode optimized for low loss performance in high frequency hard switched applications. The Stealth™ family exhibits low reverse recovery current (I<sub>RRM</sub>) and exceptionally soft recovery under typical operating conditions.

This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low  $I_{RRM}$  and short  $t_a$  phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the Stealth  $^{\rm TM}$  diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Formerly developmental type TA49409.

### **Features**

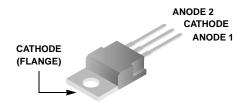
- $\begin{array}{lll} \bullet & \text{Soft Recovery.} & & t_b \, / \, t_a > 2.5 \\ \bullet & \text{Fast Recovery.} & & t_{rr} < 25 \text{ns} \\ \bullet & \text{Operating Temperature.} & & 175 \, ^{\circ}\text{C} \\ \bullet & \text{Reverse Voltage.} & & 600 \text{V} \\ \end{array}$
- · Avalanche Energy Rated

## **Applications**

- Switch Mode Power Supplies
- · Hard Switched PFC Boost Diode
- UPS Free Wheeling Diode
- · Motor Drive FWD
- SMPS FWD
- · Snubber Diode

# Package

### JEDEC TO-220AB



# K

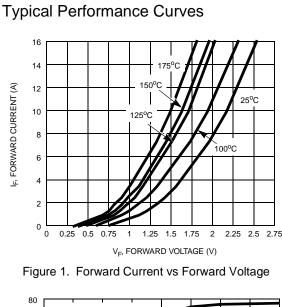
Symbol

# Device Maximum Ratings (per leg) $T_{C}$ = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{RRM}$	Peak Repetitive Reverse Voltage	600	V
V <sub>RWM</sub>	Working Peak Reverse Voltage	600	V
V <sub>R</sub>	DC Blocking Voltage	600	V
I <sub>F(AV)</sub>	Average Rectified Forward Current (T <sub>C</sub> = 147°C) Total Device Current (Both Legs)	8 16	A A
I <sub>FRM</sub>	Repetitive Peak Surge Current (20kHz Square Wave)	16	Α
I <sub>FSM</sub>	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)	100	Α
P <sub>D</sub>	Power Dissipation	85	W
E <sub>AVL</sub>	Avalanche Energy (1A, 40mH)	20	mJ
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 175	°C
T <sub>L</sub> T <sub>PKG</sub>	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10s Package Body for 10s, See Techbrief TB334	300 260	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Device	Marking	Device	Package	Tape Width	1		Quantity	
K86			TO-220AB	-			-	
Electric	al Chara	cteristics (per le	g) T <sub>C</sub> = 25°C unless	otherwise noted				
Symbol	Parameter		Test	Test Conditions		Тур	Max	Units
Off State	Characte	ristics						
I <sub>R</sub>	Instantaneous Reverse Current		V <sub>R</sub> = 600V	T <sub>C</sub> = 25°C	-	-	100	μА
1			T .	T <sub>C</sub> = 125°C	-	-	1.0	mA
On State	Character	rictics	<u>'</u>		l	l.	I.	1
V <sub>F</sub>	-	Characteristics Instantaneous Forward Voltage		T <sub>C</sub> = 25°C	_	2.0	2.4	V
٧F	Ilistantanet			$T_{\rm C} = 125^{\circ}{\rm C}$	-	1.6	2.4	V
				10 - 120 0		1.0	2.0	
Dynamic	Character	ristics						
$C_{J}$	Junction Capacitance $V_R = 10V, I_F = 0A$			-	30	-	pF	
Switching	g Characte	eristics						
t <sub>rr</sub>	Reverse Re	Reverse Recovery Time		$I_F = 1A$ , $dI_F/dt = 100A/\mu s$ , $V_R = 30V$		18	25	ns
			$I_F = 8A$ , $dI_F/dt =$	$I_F = 8A$ , $dI_F/dt = 100A/\mu s$ , $V_R = 30V$		21	30	ns
t <sub>rr</sub>	Reverse Recovery Time		I <sub>F</sub> = 8A,	$dI_F/dt = 200A/\mu s$ ,		28	-	ns
I <sub>RRM</sub>	Maximum Reverse Recovery Current					3.2	-	Α
$Q_{RR}$	Reverse Re	ecovery Charge	$V_{R} = 390V, T_{C}$	$V_R = 390V, T_C = 25^{\circ}C$		50	-	nC
t <sub>rr</sub>	Reverse Re	ecovery Time	$I_F = 8A$ ,	$dI_F/dt = 200A/\mu s,$ $V_R = 390V,$		77	-	ns
S	Softness Fa	actor (t <sub>b</sub> /t <sub>a</sub> )				3.7	-	
I <sub>RRM</sub>	Maximum F	Reverse Recovery Curre				3.4	-	Α
Q <sub>RR</sub>	Reverse Re	ecovery Charge	1 <sub>C</sub> = 125 C	$T_C = 125^{\circ}C$			-	nC
t <sub>rr</sub>	Reverse Re	ecovery Time	I <sub>F</sub> = 8A,	$dI_F/dt = 600A/\mu s$ ,		53	-	ns
S	Softness Fa	actor (t <sub>b</sub> /t <sub>a</sub> )				2.5	-	
I <sub>RRM</sub>	Maximum F	Reverse Recovery Curre		V <sub>R</sub> = 390V, T <sub>C</sub> = 125°C			-	Α
Q <sub>RR</sub>	Reverse Re	ecovery Charge	T <sub>C</sub> = 125°C				-	nC
dl <sub>M</sub> /dt	Maximum o	di/dt during t <sub>b</sub>					-	A/µs
ui <sub>M</sub> /ut								
	Characteri	istics						
	1	istics esistance Junction to Ca	se		T -	1 -	1.75	°C/W



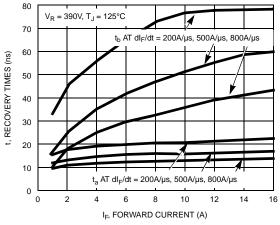


Figure 3.  $t_a$  and  $t_b$  Curves vs Forward Current

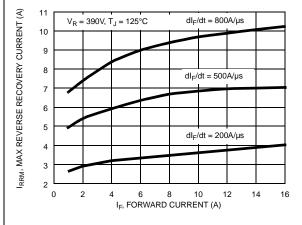


Figure 5. Maximum Reverse Recovery Current vs Forward Current

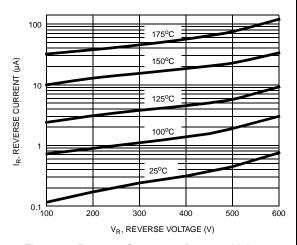


Figure 2. Reverse Current vs Reverse Voltage

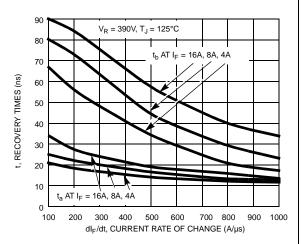


Figure 4.  $t_a$  and  $t_b$  Curves vs  $dI_F/dt$ 

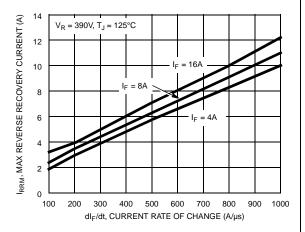
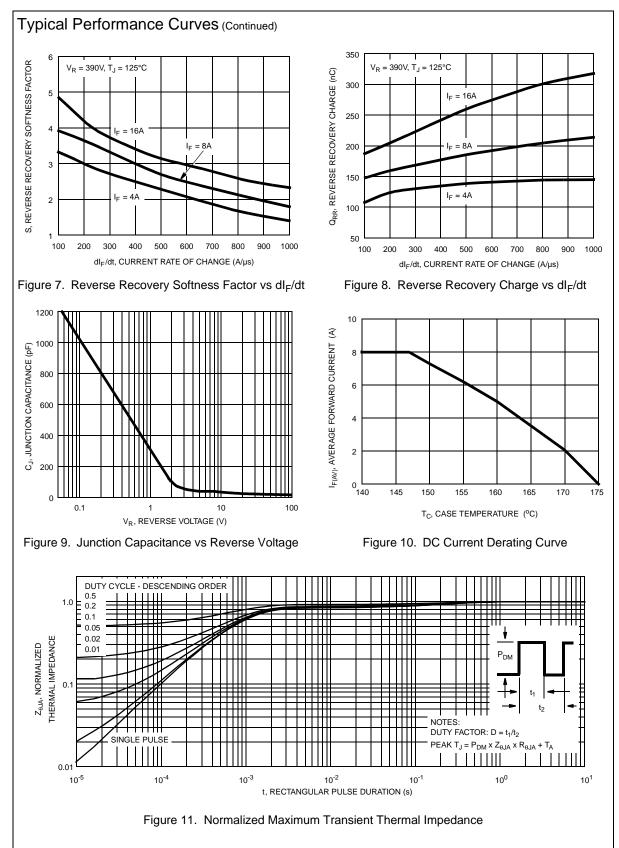


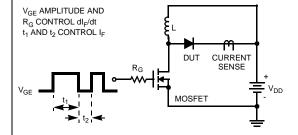
Figure 6. Maximum Reverse Recovery Current vs  $dI_F/dt$ 

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# Test Circuits and Waveforms



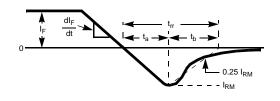


Figure 12. t<sub>rr</sub> Test Circuit

Figure 13.  $t_{rr}$  Waveforms and Definitions

```
I = 1A
L = 40mH
R < 0.1\Omega
V_{DD} = 50V
E_{AVL} = 1/2LI^2 \left[ V_{R(AVL)}/(V_{R(AVL)} - V_{DD}) \right]
Q_1 = IGBT \left( BV_{CES} > DUT V_{R(AVL)} \right)
CURRENT
SENSE
V_{DD}
DUT
```

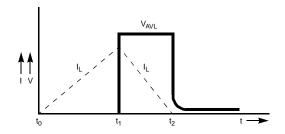


Figure 14. Avalanche Energy Test Circuit

Figure 15. Avalanche Current and Voltage Waveforms

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